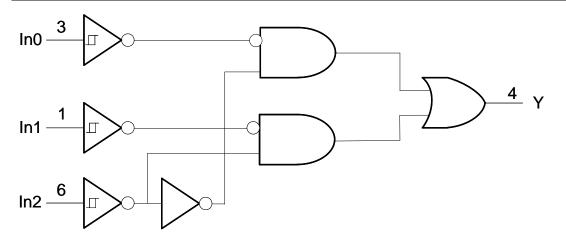


### **Pin Descriptions**

Pin Name	Description
IN1	Data Input
GND	Ground
IN0	Data Input
Υ	Data Output
Vcc	Supply Voltage
IN2	Data Input

### **Logic Diagram**

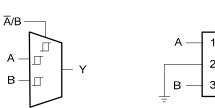


### **Function Table**

	Inputs		Output
IN2	IN2 IN1		Y
L	L	L	L
L	L	Н	L
L	Н	L	Н
L	Н	Н	Н
Н	L	L	L
Н	L	Н	Н
Н	Н	L	L
Н	Н	Н	Н



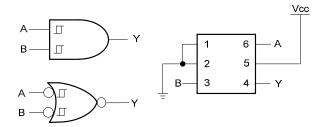
### **Logic Configurations**



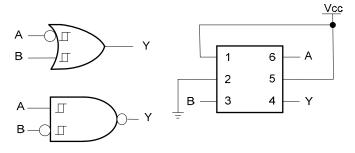
A — 1 6 — Ā/B

2 5
3 4 — Y

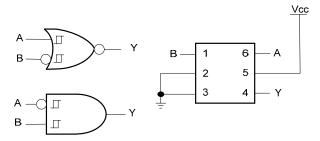
Configuration 1
2 to 1 Data Selector



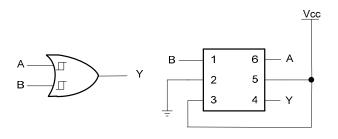
Configuration 2 2-Input AND Gate 2-Input NOR Gate with Both Inputs Inverted



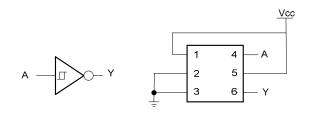
Configuration 3
2-Input NAND Gate with B Input Inverted
2-Input OR Gate with A Input Inverted



Configuration 4
2-Input NOR Gate with One Input Inverted
2-Input AND Gate with One Input Inverted



Configuration 5 2-Input OR Gate



Configuration 6 Inverter

Function Selection Table							
Logic Function	Configuration						
2-to-1 Data Selector	1						
2-input AND gate	2						
2-input AND with inverted input	3, 4						
2-input NOR with inverted input	3, 4						
2-input OR	5						
2-input NOR with both inputs inverted	2						
1-input Inverter	6						



### **Absolute Maximum Ratings (Note 4)**

Symbol	Description	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	KV
ESD MM	Machine Model ESD Protection	200	V
V <sub>CC</sub>	Supply Voltage Range	-0.5 to 6.5	V
VI	Input Voltage Range	-0.5 to 6.5	V
Vo	Voltage applied to output in high impedance or I <sub>OFF</sub> state	-0.5 to 6.5	V
Vo	Voltage applied to output in high or low state	-0.3 to V <sub>CC</sub> +0.5	V
l <sub>IK</sub>	Input Clamp Current V <sub>I</sub> < 0	-50	mA
lok	Output Clamp Current	-50	mA
Io	Continuous output current	±50	mA
	Continuous current through Vdd or GND	±100	mA
TJ	Operating Junction Temperature	-40 to +150	°C
T <sub>STG</sub>	Storage Temperature	-65 to +150	°C

Notes: 4. Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.

### **Recommended Operating Conditions (Note 5)**

Symbol		Parameter	Min	Max	Unit	
.,,	On and the a Mallana	Operating	1.65	5.5	V	
Vcc	Operating Voltage	Data retention only	1.5		V	
VI	Input Voltage		0	5.5	V	
Vo	Output Voltage		0	V <sub>CC</sub>	٧	
		V <sub>CC</sub> = 1.65V		-4		
		V <sub>CC</sub> = 2.3V		-8		
I <sub>OH</sub>	High-level output current	V <sub>CC</sub> = 3V		-16	mA	
				-24		
		V <sub>CC</sub> = 4.5V		-32		
		V <sub>CC</sub> = 1.65V		4		
		V <sub>CC</sub> = 2.3V		8		
loL	Low-level output current			16	mA	
		$V_{CC} = 3V$		24		
		V <sub>CC</sub> = 4.5V		32		
		V <sub>CC</sub> = 1.8V ± 0.15V, 2.5V ± 0.2V		20		
Δt/ΔV	Input transition rise or fall rate	V <sub>CC</sub> = 3.3V ± 0.3V		10	ns/V	
		V <sub>CC</sub> = 5V ± 0.5V		5		
T <sub>A</sub>	Operating free-air temperature		-40	+125	°C	

Notes: 5. Unused inputs should be held at  $V_{\text{CC}}$  or Ground.



## Electrical Characteristics $T_A = -40$ °C to +85°C (All typical values are at $V_{CC} = 3.3$ V, $T_A = +25$ °C)

Symbol	Parameter	Test Conditions	Vcc	Min	Тур	Max	Unit
			1.65V	0.70		1.20	
			2.3V	1.11		1.60	
$V_{T+}$	Positive-going input threshold voltage		3V	1.50		2.00	
	tillesiloid voltage		4.5V	2.16		2.74	
			5.5V	2.61		3.33	
			1.65V	0.30		0.72	
	Negative-going input threshold voltage		2.3V	0.58		1.00	
V <sub>T-</sub>			3V	0.80		1.30	
	tillesiloid voltage		4.5V	1.21		1.95	
			5.5V	1.45		2.35	
			1.65V	0.30		0.62	
			2.3V	0.40		0.80	
$\Delta V_T$	Hysteresis (V <sub>T+</sub> - V <sub>T-)</sub>		3V	0.35		1.00	
			4.5V	0.55		1.10	
			5.5V	0.60		1.20	
		I <sub>OH</sub> = -100μA	1.65V to 5.5V	V <sub>CC</sub> - 0.1			
		$I_{OH} = -4mA$	1.65V	1.2			
		$I_{OH} = -8mA$	2.3V	1.9			.,,
V <sub>OH</sub>	High Level Output Voltage	I <sub>OH</sub> = -16mA	0) /	2.4			V
		I <sub>OH</sub> = -24mA	3V	2.3			
		I <sub>OH</sub> = -32mA	4.5V	3.8			
		$I_{OL} = 100 \mu A$	1.65V to 5.5V			0.1	
		$I_{OL} = 4mA$	1.65V			0.45	
	LP of Level Level Voltage	I <sub>OL</sub> = 8mA	2.3V			0.3	
V <sub>OL</sub>	High-level Input Voltage	I <sub>OL</sub> = 16mA	2) /			0.4	V
		I <sub>OL</sub> = 24mA	3V			0.55	
		$I_{OL} = 32mA$	4.5V			0.55	
l <sub>l</sub>	Input Current	V <sub>I</sub> = 5.5V or GND	0 to 5.5V			± 5	μA
l <sub>OFF</sub>	Power Down Leakage Current	$V_1$ or $V_0 = 5.5V$	0			± 10	μA
Icc	Supply Current	V <sub>I</sub> = 5.5V of GND Io=0	1.65V to 5.5V			10	μΑ
ΔI <sub>CC</sub>	Additional Supply Current	One input at V <sub>CC</sub> –0.6V Other inputs at V <sub>CC</sub> or GND	3V to 5.5V			500	μΑ



## Electrical Characteristics $T_A = -40$ °C to +125°C (All typical values are at $V_{CC} = 3.3$ V, $T_A = +25$ °C)

Symbol	Parameter	Test Conditions	Vcc	Min	Тур	Max	Unit
			1.65V	0.70		1.20	
			2.3V	1.11		1.60	
$V_{T+}$	Positive-going input threshold voltage		3V	1.50		2.00	
	tillesiloid voltage		4.5V	2.16		2.74	
			5.5V	2.61		3.33	
			1.65V	0.30		0.75	
	No notice and a found		2.3V	0.58		1.03	
$V_{T-}$	Negative-going input threshold voltage		3V	0.80		1.33	
	tillesiloid voltage		4.5V	1.21		1.95	
			5.5V	1.45		2.35	
			1.65V	0.30		0.62	
			2.3V	0.37		0.80	
$\Delta V_{T}$	Hysteresis (V <sub>T+</sub> - V <sub>T-)</sub>		3V	0.32		1.00	
			4.5V	0.50		1.20	
			5.5V	0.55		1.40	
		I <sub>OH</sub> = -100μA	1.65V to 5.5V	V <sub>CC</sub> -0.1			ı
		$I_{OH} = -4mA$	1.65V	0.95			
\/	Liber Lavel Outent Valtage	$I_{OH} = -8mA$	2.3V	1.7			\ /
$V_{OH}$	High Level Output Voltage	I <sub>OH</sub> = -16mA	2)./	1.9			V
		I <sub>OH</sub> = -24mA	3V	2.0			
		I <sub>OH</sub> = -32mA	4.5V	3.4			
		$I_{OL} = 100\mu A$	1.65V to 5.5V			0.1	
		$I_{OL} = 4mA$	1.65V			0.7	
		$I_{OL} = 8mA$	2.3V			0.45	.,
$V_{OL}$	High-level Input Voltage	I <sub>OL</sub> = 16mA	0)/			0.6	V
		I <sub>OL</sub> = 24mA	3V			0.8	
		I <sub>OL</sub> = 32mA	4.5V			0.8	
II	Input Current	V <sub>I</sub> = 5.5V or GND	0 to 5.5V			± 100	μΑ
l <sub>OFF</sub>	Power Down Leakage Current	$V_I$ or $V_O = 5.5V$	0			± 200	μΑ
Icc	Supply Current	V <sub>I</sub> = 5.5V of GND I <sub>O</sub> =0	1.65V to 5.5V			200	μΑ
ΔI <sub>CC</sub>	Additional Supply Current	One input at V <sub>CC</sub> -0.6V Other inputs at V <sub>CC</sub> or GND	3V to 5.5V			5000	μA



### Electrical Characteristics (All typical values are at $V_{CC} = 3.3V$ , $T_A = +25$ °C)

Symbol	Parameter	Test Conditions	Vcc	Min	Тур	Max	Unit
Cı	Input Capacitance	$V_I = V_{CC} - \text{or GND}$	3.3		3.5		pF
		SOT26			204		
	Thermal Resistance Junction-	SOT363	(Note 6)		371		0=
θ <sub>JA</sub>	to-Ambient	X2-DFN1410-6			430		°C/W
		X2-DFN1010-6			510		
		SOT26			52		
	Thermal Resistance Junction-	SOT363	(Note 6)		143		°C/W
θ <sub>JC</sub>	to-Case	X2-DFN1410-6			190		
		X2-DFN1010-6			250		

Notes:

### **Switching Characteristics**

 $T_A = -40$ °C to +85°C,  $C_L = 30$  or 50pF as noted (see Figure 1)

Parameter	From	_	± U			: 2.5V ).2V		: 3.3V ).3V	V <sub>CC</sub>	= 5V .5V	Unit
	(Input)		Min	Max	Min	Max	Min	Max	Min	Max	
t <sub>pd</sub>	Any	Y	1.0	14.4	0.7	8.3	0.7	6.3	0.7	5.1	ns

 $T_A = -40$ °C to +125°C,  $C_L = 30$  or 50pF as noted (see Figure 1)

Parameter	From	то	V <sub>CC</sub> = 1.8V ± 0.15V			: 2.5V .2V		: 3.3V ).3V	V <sub>CC</sub>	= 5V .5V	Unit
	(Input) (	(Input) (OUTPUT)	Min	Max	Min	Max	Min	Max	Min	Max	
t <sub>pd</sub>	Any	Υ	1.0	18.0	0.7	10.4	0.7	7.9	0.7	6.4	ns

### **Operating Characteristics**

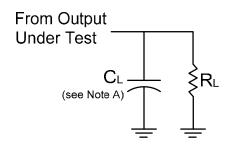
 $T_A = +25$ °C

Parameter		Test Conditions	V <sub>CC</sub> = 1.8V Typ.	V <sub>CC</sub> = 2.5V Typ.	V <sub>CC</sub> = 3.3V Typ.	V <sub>CC</sub> = 5V Typ.	Unit
$C_{pd}$	Power dissipation capacitance	f = 10 MHz	22	22	23	24	pF

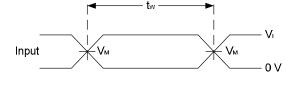
<sup>6.</sup> Test condition for SOT26, SOT363, X2-DFN1410-6 and X2-DFN1010-6 : Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.



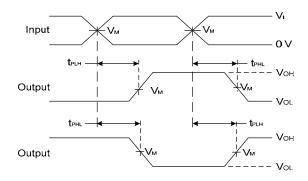
#### **Parameter Measurement Information**



Vcc	In	puts	V <sub>M</sub>	CL	R∟
100	VI	t <sub>r</sub> /t <sub>f</sub>	- 141	52	
1.8V±0.15V	V <sub>CC</sub>	≤2ns	V <sub>CC</sub> /2	30pF	1ΚΩ
2.5V±0.2V	V <sub>CC</sub>	≤2ns	V <sub>CC</sub> /2	30pF	500Ω
3.3V±0.3V	3V	≤2.5ns	1.5V	50pF	500Ω
5V±0.5V	V <sub>CC</sub>	≤2.5ns	V <sub>CC</sub> /2	50pF	500Ω



Voltage Waveform Pulse Duration



Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs

Figure 1. Load Circuit and Voltage Waveforms

Notes: A. Includes test lead and test apparatus capacitance.

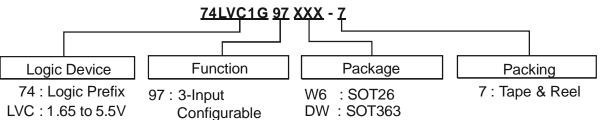
B. All pulses are supplied at pulse repetition rate ≤ 10 MHz

C. Inputs are measured separately one transition per measurement

D. t<sub>PLH</sub> and t<sub>PHL</sub> are the same as t<sub>PD</sub>



### **Ordering Information**



Family Multiple-Function FW4: X2-DFN1010-6
1G: One gate Gate FZ4: X2-DFN1410-6

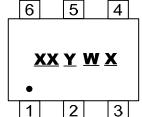
	Davis Onto	Packaging 7" Tape and Reel		and Reel	
	Device	Package Code	(Note 7)	Quantity	Part Number Suffix
Pb,	74LVC1G97W6-7	W6	SOT26	3000/Tape & Reel	-7
Pb,	74LVC1G97DW-7	DW	SOT363	3000/Tape & Reel	-7
Pb	74LVC1G97FW4-7	FW4	X2-DFN1010-6	5000/Tape & Reel	-7
Pb	74LVC1G97FZ4-7	FZ4	X2-DFN1410-6	5000/Tape & Reel	-7

Notes: 7. Pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.



### **Marking Information**

#### (1) SOT26, SOT363



74LVC1G97DW

XX: Identification code

Y: Year 0~9

<u>W</u>: Week: A~Z: 1~26 week;

a~z: 27~52 week; z represents

52 and 53 week X: A~Z: Internal Code

Part Number	Package	Identification Code
74LVC1G97W6	SOT26	TY

SOT363

#### (2) X2-DFN1010-6, X2-DFN1410-6

#### (Top View)



XX: Identification Code

 $\overline{\underline{Y}}$  : Year : 0~9

\overline{\text{\Week}}: A~Z : 1~26 week; a~z : 27~52 week; z represents

ΤY

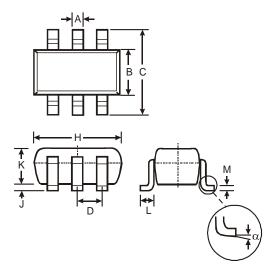
52 and 53 week X : A~Z : Internal code

Part Number	Package	Identification Code
74LVC1G97FW4	X2-DFN1010-6	TY
74LVC1G97FZ4	X2-DFN1410-6	TY



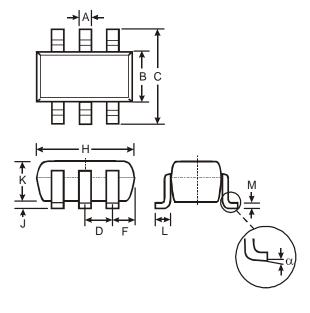
### Package Outline Dimensions (All Dimensions in mm)

#### (1) SOT26



SOT26			
Dim	Min	Max	Тур
Α	0.35	0.50	0.38
В	1.50	1.70	1.60
O	2.70	3.00	2.80
D	_		0.95
Н	2.90	3.10	3.00
7	0.013	0.10	0.05
K	1.00	1.30	1.10
L	0.35	0.55	0.40
M	0.10	0.20	0.15
α	0°	8°	_
All Dimensions in mm			

#### (2) SOT363

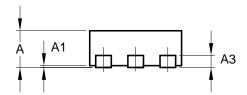


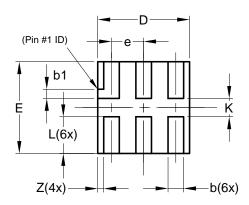
SOT363				
Dim	Min	Max		
Α	0.10	0.30		
В	1.15	1.35		
O	2.00	2.20		
D	0.65 Typ			
F	0.40	0.45		
H	1.80	2.20		
۲	0	0.10		
K	0.90	1.00		
Г	0.25	0.40		
М	0.10	0.22		
α	0°	8°		
All Dimensions in mm				



### Package Outline Dimensions (All Dimensions in mm)

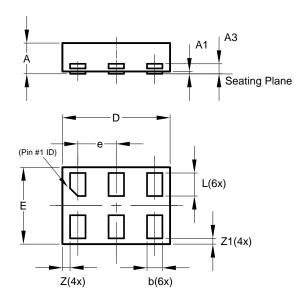
#### (3) X2-DFN1010-6





X2-DFN1010-6				
Dim	Min	Max	Тур	
Α	_	0.40	0.39	
A1	0.00	0.05	0.02	
А3	_	_	0.13	
b	0.14	0.20	0.17	
b1	0.05	0.15	0.10	
D	0.95	1.05	1.00	
Е	0.95	1.05	1.00	
е	_	_	0.35	
L	0.35	0.45	0.40	
K	0.15		_	
Z	_		0.065	
All Dimensions in mm				

### (4) X2-DFN1410-6

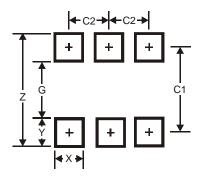


X2-DFN1410-6			
Dim	Min	Max	Тур
Α		0.40	0.39
A1	0.00	0.05	0.02
А3		_	0.13
b	0.15	0.25	0.20
D	1.35	1.45	1.40
Е	0.95	1.05	1.00
е	_	_	0.50
L	0.25	0.35	0.30
Z		_	0.10
<b>Z</b> 1	0.045	0.105	0.075
All Dimensions in mm			



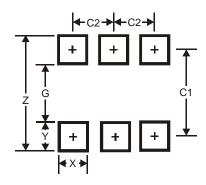
### **Suggest Pad Layout**

#### (1) SOT26



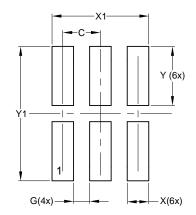
Dimensions	Value (in mm)
Z	3.20
G	1.60
Х	0.55
Y	0.80
C1	2.40
C2	0.95

#### (2) SOT363



Dimensions	Value (in mm)
Z	2.5
G	1.3
Х	0.42
Υ	0.6
C1	1.9
C2	0.65

#### (3) X2-DFN1010-6

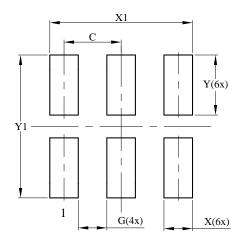


Dimensions	Value (in mm)
C	0.350
G	0.150
Х	0.200
X1	0.900
Y	0.550
Y1	1 250



### **Suggest Pad Layout**

#### (4) X2-DFN1410-6



Dimensions	Value
Difficusions	(in mm)
С	0.500
G	0.250
X	0.250
X1	1.250
Y	0.525
Y1	1.250



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